

Scalable and Accurate Modelling of a WBG-based Bidirectional DC/DC Converter for Electric Drivetrains

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Power Electronics Drives: Demand



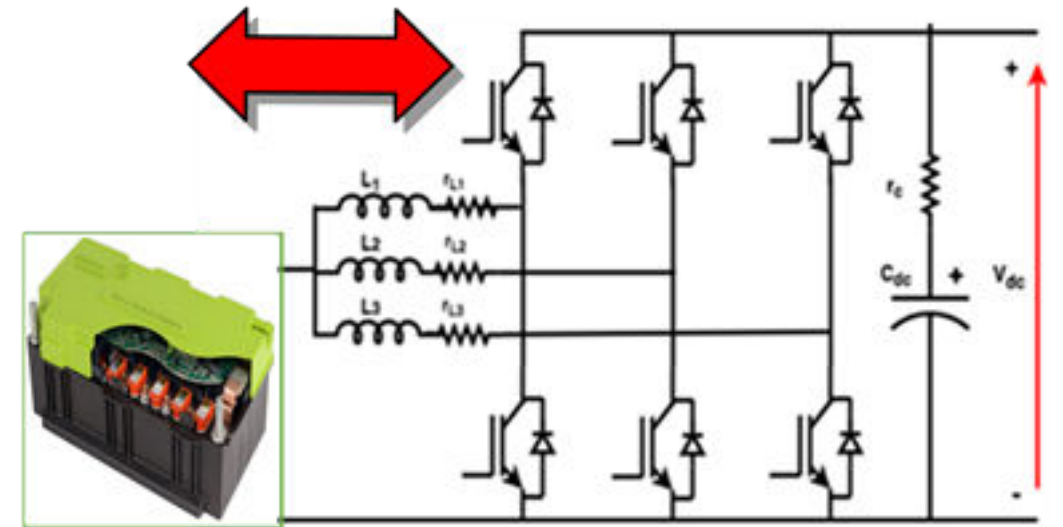
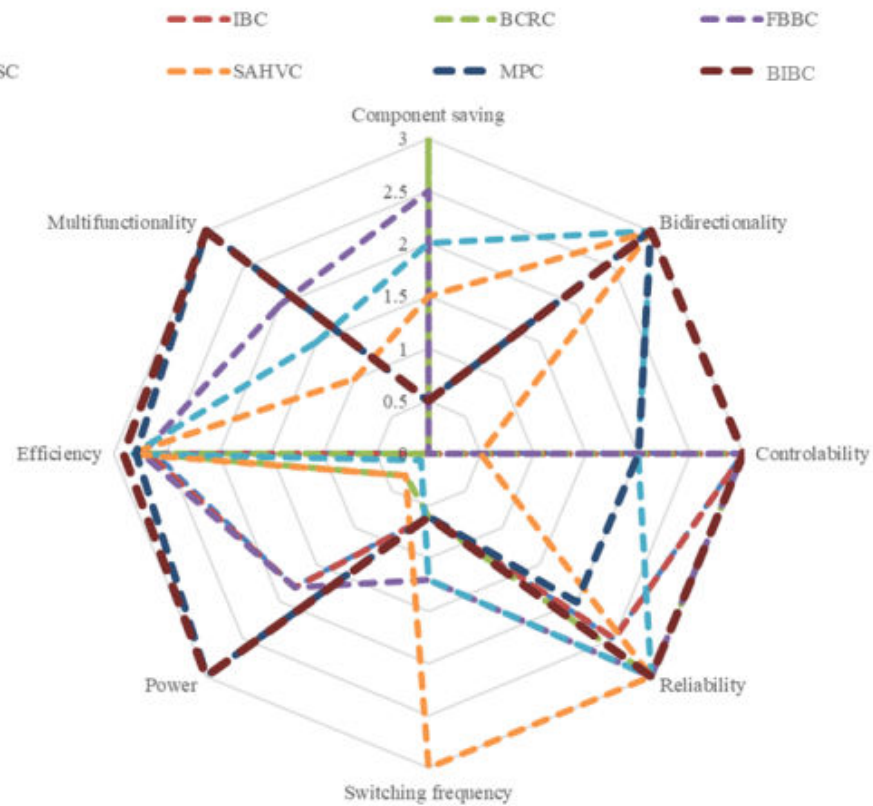
Power Electronics Drives: Challenges



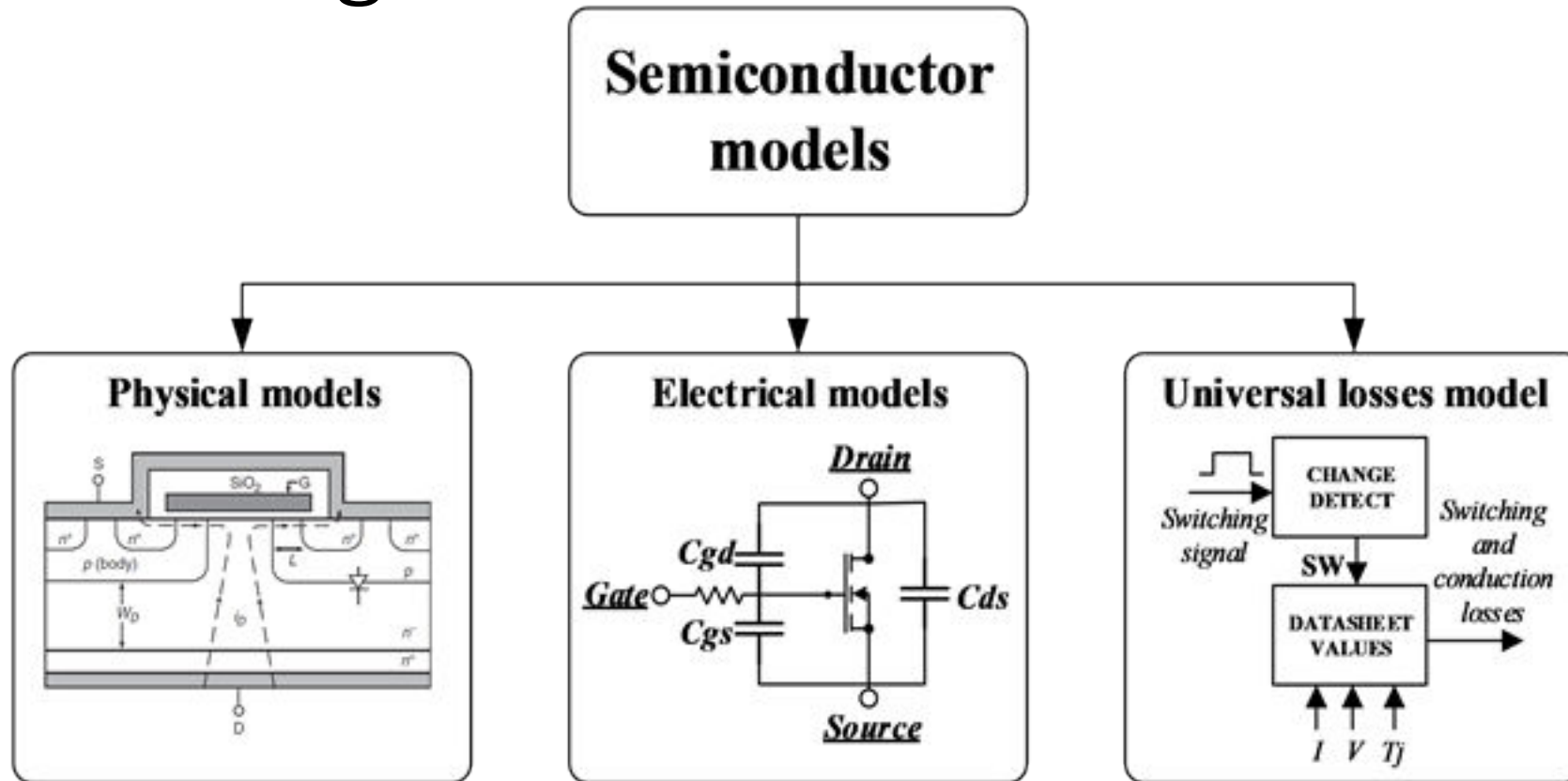
Contents

- ❑ DC/DC Topology Selection for EVs
- ❑ High Fidelity (HiFi) Modelling Approach
 - ✓ Device Modelling
 - ✓ Passive Components Modelling
- ❑ Scalability & Accuracy
- ❑ Impact of WBGs on Converter Performance
- ❑ Conclusion

HV DC/DC Topology Selection for EVs



Device Modelling



HiFi Switch Modelling

Electrical and thermal variables integration

❑ Multiphysical Nodes

- ❑ Control: Gate (G)
- ❑ Electric: Drain/Collector (D/C) – Source/Emitter (S/E)
- ❑ Thermal Node: Junction (j)

❑ Main Internal Variables

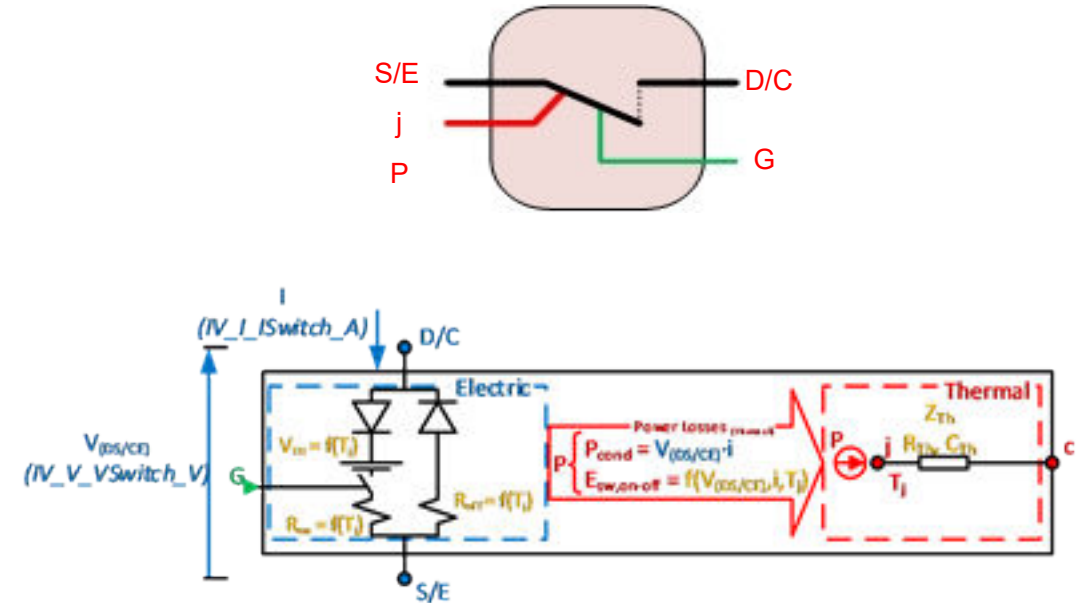
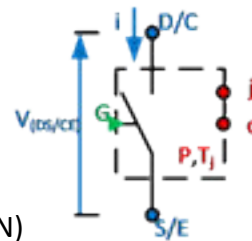
- ❑ Electric: $\{v, i\}$
- ❑ Thermal: $\{T_j, Q \equiv P_{\text{Loss}} \rightarrow [E_{\text{Sw,On}}, E_{\text{Sw,Off}}, P_{\text{Sw,On}}, P_{\text{Sw,Off}}, P_{\text{cond}}]\}$

❑ Main Parameters

- ❑ Electric: $\{R_{\text{DS,ON}}(T_j), V_{\text{th}}(T_j), R_{\text{OFF}}\}$
 - ❑ Adaptable to any switch technology (Si, SiC, GaN)
- ❑ Thermal: $\{E_{\text{Sw,On}}(\text{LUT})(T_j, i, v), E_{\text{Sw,Off}}(\text{LUT})(T_j, i, v)\}$ - By means of LookUp Tables (LUT)

❑ Output

- ❑ $P \equiv P_{\text{Loss}}$
- MOBILITY, LOGISTICS &
AUTOMOTIVE TECHNOLOGY
RESEARCH CENTRE



HiFi Diode Modelling

Electrical and thermal variables integration

□ Multiphysical Nodes

- Electric: Anode (a) – Cathode (k).
- Thermal: Junction (j).

□ Main Internal Variables

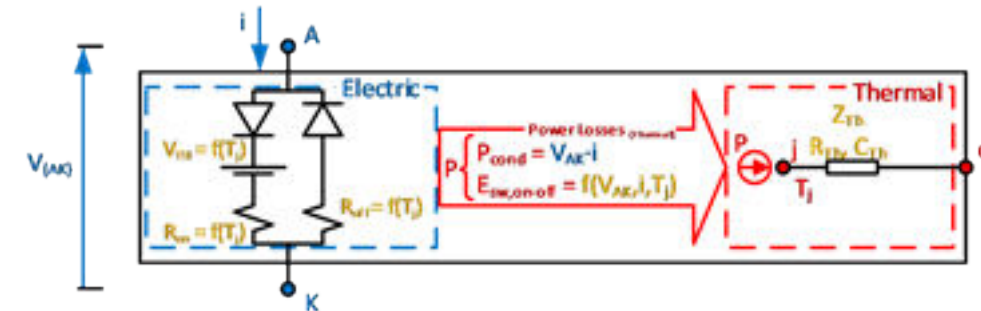
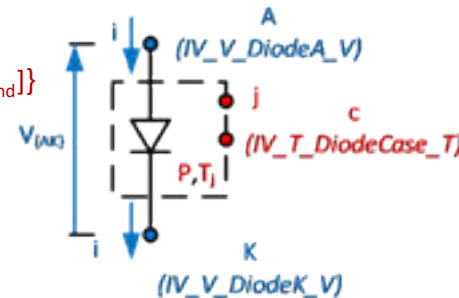
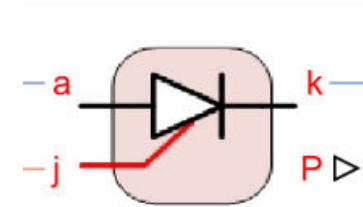
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□ Main Parameters

- Electric: $\{R_{\text{ON}}(T_j), V_{\text{th}}(T_j), R_{\text{OFF}}(T_j)\}$
 - Adaptable to any switch technology (Si, SiC)
- Thermal: $\{E_{\text{Sw,On}}(\text{LUT})(T_j, i, v), E_{\text{Sw,Off}}(\text{LUT})(T_j, i, v)\}$ - By means of LookUp Tables (LUT)

□ Output

- $P \equiv P_{\text{Loss}}$



HiFi Passive Component Modelling

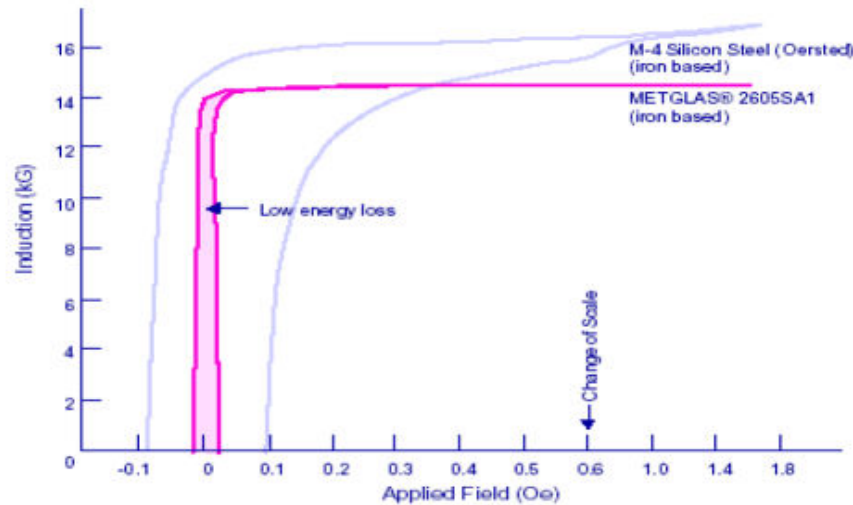


Fig: Selection of high-performance material

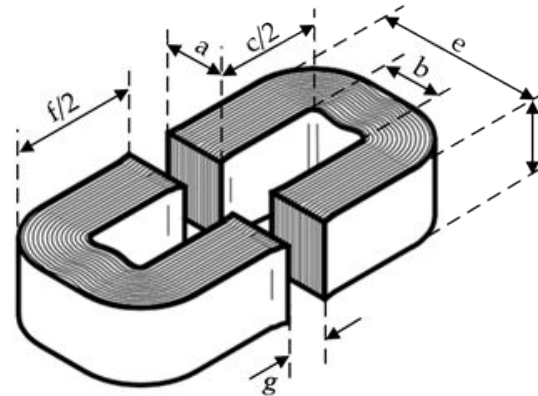


Fig: Geometry parameters of selected core

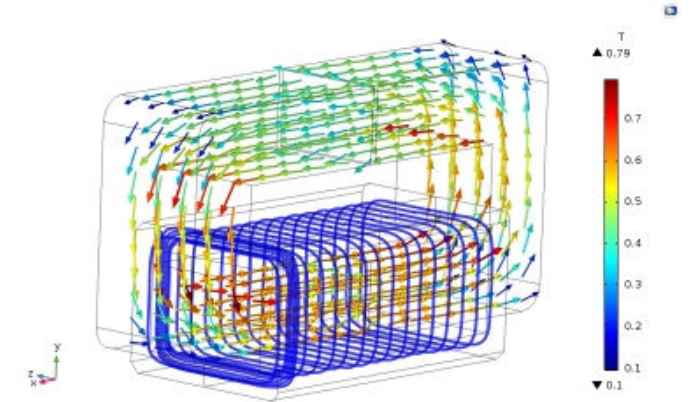


Fig: FEM Analysis of selected Inductor

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$$ESR = \frac{R_2}{1 + (2\pi f)^2 C_2^2 R_2^2} + R_1 + R_0$$



Fig: Polypropylene, DC Link Capacitors

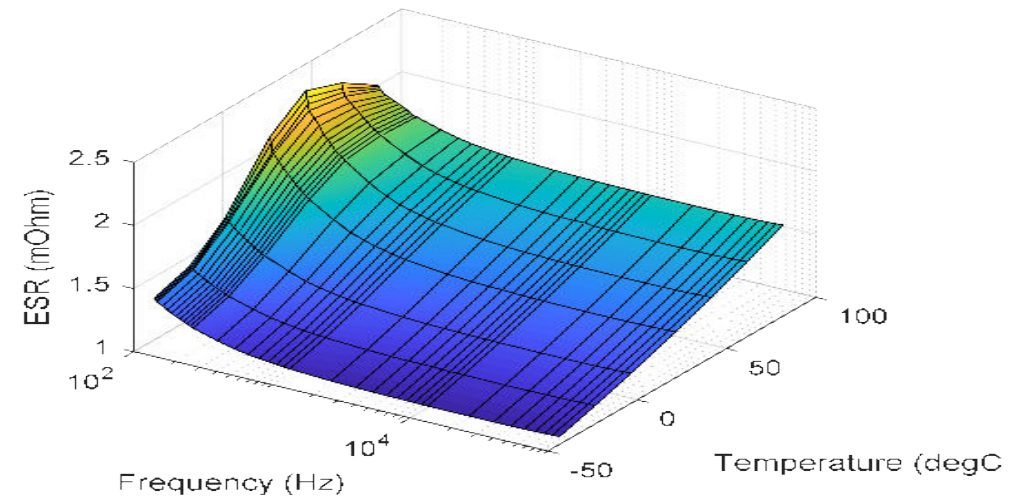
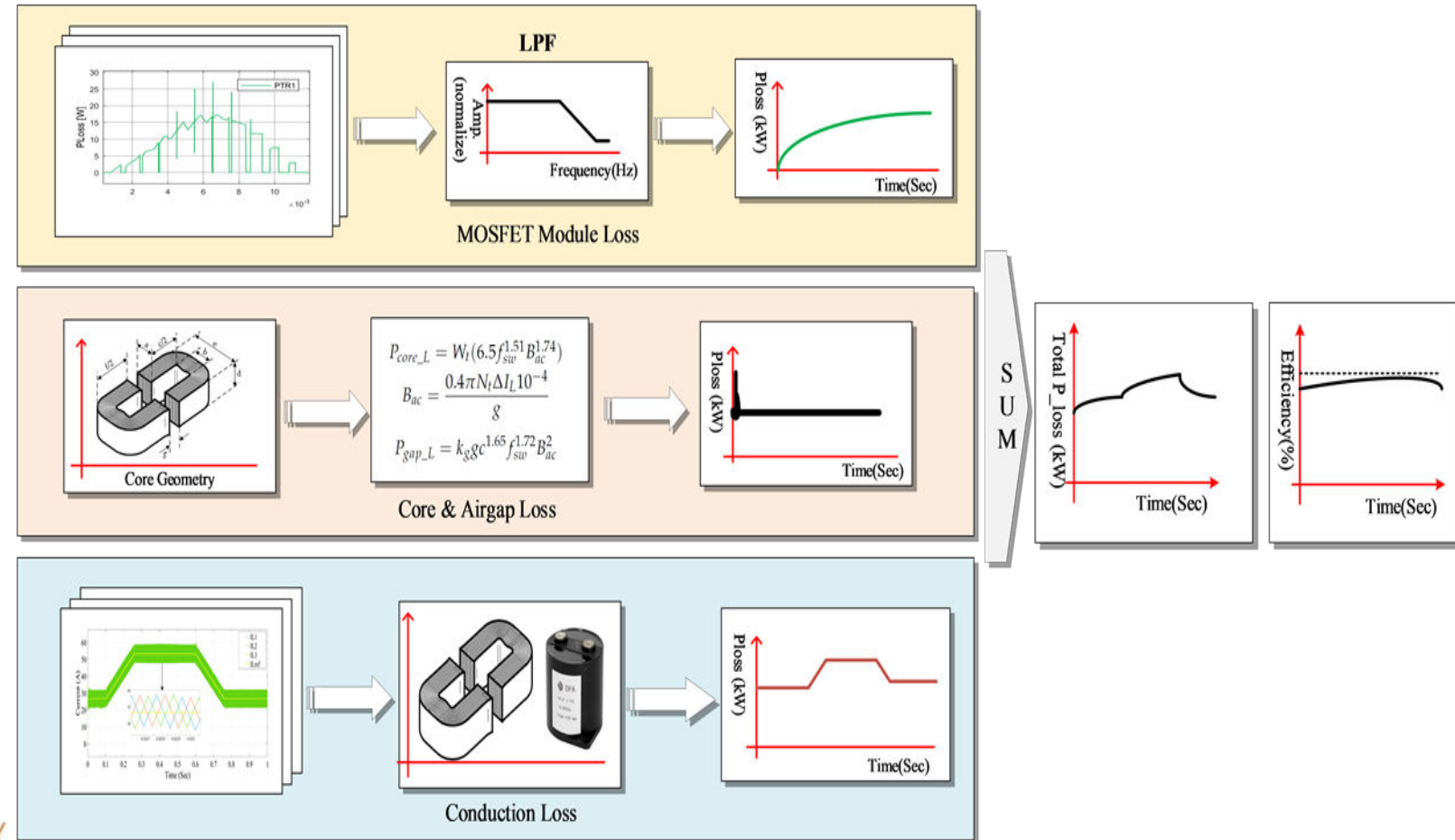


Fig: ESR model of capacitors

HiFi Loss Modelling



Scalability

Description	Special HiFi	HiFi	LoFi
Model Type	Simscape + Simulink	Simulink	Simulink
Step size	1e-6	1e-6 or 1e-7	1e-2
Variants type	15×3 (45)	3×6×5×5 (450)	15×3×3 (135)
Sensor Type	HiFi	Ideal	Ideal
Loss model	Instantaneous	Instantaneous	Average
Thermal model	HiFi	HiFi	Map based
Safety functionalities	Yes	Yes	Yes
xMOD compatibility	No	Yes	Yes
HiL capacity	No	Yes	Yes
Characteristics	✓ Accurate physics	✓ Accurate physics	✓ Map based
	✓ Dual-loop lead-lag control	✓ Dual-loop lead-lag control	✓ Faster than RT
	✓ Discrete control	✓ Discrete control	✓ Device selection
	✓ Short-circuit simulation	✓ dv/dt analysis	
	✓ dv/dt analysis	✓ Less simulation time than Special HiFi	
	✓ Detail parameterization	✓ Detail parameterization	
	✓ Complex final integration		
Limitations	✓ High simulation time	✓ No Short-circuit simulation	✓ No semiconductor physics

Accuracy

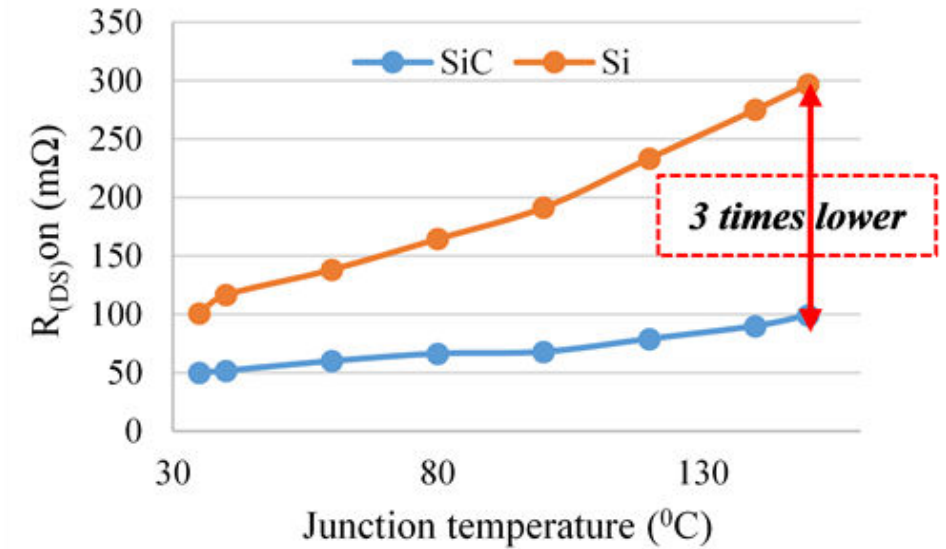
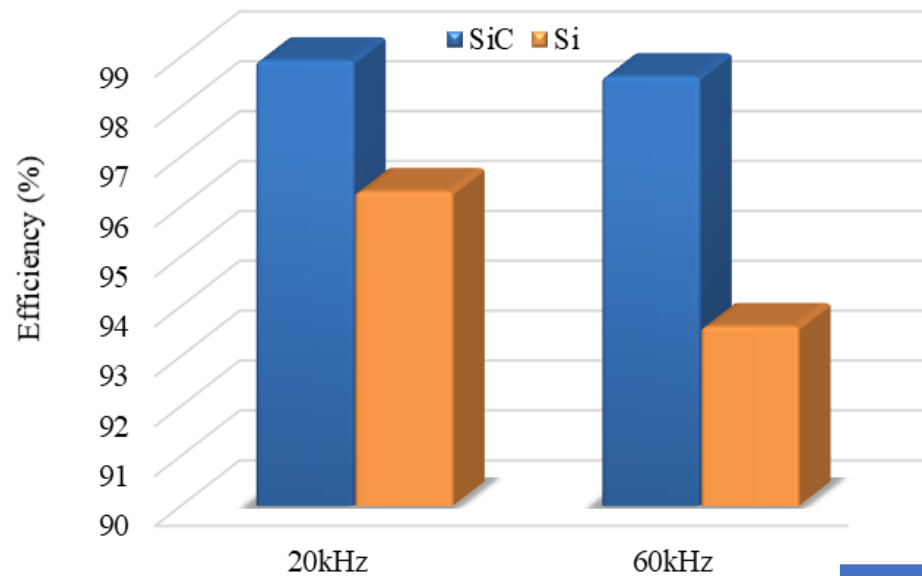
Error between different model

Model	Average Power Losses	Average Junction Temperature	Average DC Link Current
Special HiFi	0%	0%	0%
HiFi	2.03 %	0.55 %	0.55 %
LoFi	5.29 %	0.61 %	3.49 %

FEM and Experimental result

AMCC50	FEM (μH)	Experimental (μH) Prototype	Error
Number of turns=19; Airgap=0.8mm	155.49	164.8	5.65%
Losses	10.37	10.50	1.23%

Impact of WBGs on Converter Performance



Parameter	Value
Rated Power, P_{nom}	30kW
DC Link Voltage, V_o	400V
Input Voltage, V_{BAT}	200V
Input current, I_{in}	150A

Conclusion

- ☐ High Fidelity simulations use for system characterizations & validation
- ☐ Improve scalability, modularity and real-time use of simulations
- ☐ Achieve time reduction in model to model calibration
- ☐ Targeting reduction in co-simulation toolchain
- ☐ High potential using WBGs

Future work

- ☐ Validate regarding experimental result

Thank you for your attention



LET'S TALK